

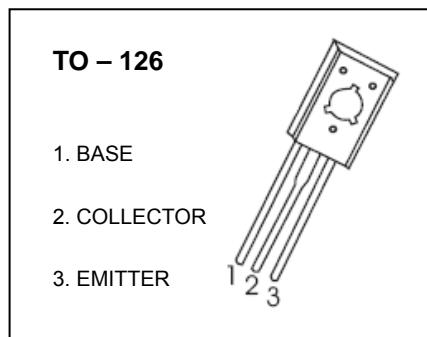


TO-126 Plastic-Encapsulate Transistors

TIP29 Series TRANSISTOR (NPN)

FEATURES

- Designed for Use in General Purpose Amplifier and Switching Applications



MAXIMUM RATINGS ($T_a=25^\circ\text{C}$ unless otherwise noted)

Symbol	Parameter	Value	Unit
V_{CBO}	Collector-Base Voltage	TIP29	V
		TIP29A	
		TIP29B	
		TIP29C	
V_{CEO}	Collector-Emitter Voltage	TIP29	V
		TIP29A	
		TIP29B	
		TIP29C	
V_{EBO}	Emitter-Base Voltage	5	V
I_c	Collector Current(DC)	1	A
I_{cp}	Collector Current(Pulse)	3	A
P_c	Collector Power Dissipation	1.25	W
$R_{\theta JA}$	Thermal Resistance From Junction To Ambient	100	$^\circ\text{C}/\text{W}$
T_j	Junction Temperature	150	$^\circ\text{C}$
T_{stg}	Storage Temperature	-55~+150	$^\circ\text{C}$

ELECTRICAL CHARACTERISTICS ($T_a=25^\circ\text{C}$ unless otherwise specified)

Parameter	Symbol	Test conditions	Min	Typ	Max	Unit
Collector-base breakdown voltage	$V_{(BR)CBO}$	$I_C=100\mu\text{A}, I_E=0$	TIP29	40		V
			TIP29A			
			TIP29B			
			TIP29C			
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	$I_C=30\text{mA}, I_B=0$	TIP29	40		V
			TIP29A	60		
			TIP29B	80		
			TIP29C	100		
Emitter-base breakdown voltage	$V_{(BR)EBO}$	$I_E=100\mu\text{A}, I_C=0$	5			V
Collector cut-off current	I_{CEO}	$V_{CE}=30\text{V}, I_B=0$	TIP29/29A		0.3	mA
		$V_{CE}=60\text{V}, I_B=0$	TIP29B/29C			
Collector cut-off current	I_{CES}	$V_{CE}=40\text{V}, V_{EB}=0$	TIP29		200	μA
		$V_{CE}=60\text{V}, V_{EB}=0$	TIP29A		200	
		$V_{CE}=80\text{V}, V_{EB}=0$	TIP29B		200	
		$V_{CE}=100\text{V}, V_{EB}=0$	TIP29C		200	

Emitter cut-off current	I_{EBO}	$V_{EB}=5V, I_C=0$			1	mA
DC current gain	$h_{FE(1)}^*$	$V_{CE}=4V, I_C=0.2A$	40			
	$h_{FE(2)}^*$	$V_{CE}=4V, I_C=1A$	15		75	
Collector-emitter voltage	$V_{CE(sat)}^*$	$I_C=1A, I_B=125mA$			0.7	V
Base-emitter saturation voltage	V_{BE}^*	$V_{CE}=4V, I_C=1A$			1.3	V
Transition frequency	f_T	$V_{CE}=10V, I_C=200mA$	3			MHz

*Pulse test: pulse width $\leq 300\mu s$, duty cycle $\leq 2.0\%$.